

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 56-084618

(43)Date of publication of application : 10.07.1981

(51)Int.Cl.

B01D 53/34
C30B 31/16

(21)Application number : 54-161896

(71)Applicant : SEITETSU KAGAKU CO LTD
NIPPON SANGYO GIJUTSU KK

(22)Date of filing : 12.12.1979

(72)Inventor : KARAKI TADASHI
IKETANI YOSHIKAZU
NAJIMA TOMOHARU
AOKI KAORU

(54) METHOD OF REMOVING HARMFUL GAS FOR SEMICONDUCTOR

(57)Abstract:

PURPOSE: To remove harmful gases for semiconductors virtually perfectly by absorbing the gases for semiconductors by using a rotary type fine foam generator and using an aqueous potassium permanganate soln. as absorbing liquid.

CONSTITUTION: Gases for semiconductors such as arsine, phosphine, and diborane are absorbed and removed by using an aqueous potassium permanganate as absorbing liquid and using a rotary type fine foam generator. For example, 3l aqueous potassium permanganate soln. of 2.0wt% is put into a "Rotary Atomizer Model TOPCA-L-2", and while a rotor is being rotated at 2,000W2,500rpm, an N2 gas contg. 100W20,000ppm arsine is introduced therein at the rate of 2W10l/min. The arsine concn. at the outlet is ≤ 0.5 ppm. The suitable concn. of the aqueous potassium permanganate is 0.2W5.0wt%.

LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]